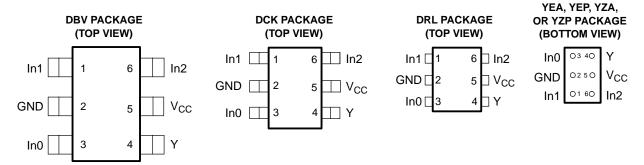
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FEATURES

- Available in the Texas Instruments
 NanoStar[™] and NanoFree[™] Packages
- Low Static-Power Consumption ($I_{CC} = 0.9 \mu A$ Max)
- Low Dynamic-Power Consumption (C_{pd} = 4.3 pF Typ at 3.3 V)
- Low Input Capacitance (C_i = 1.5 pF Typ)
- Low Noise Overshoot and Undershoot <10% of V_{CC}
- I_{off} Supports Partial-Power-Down Mode Operation
- Includes Schmitt-Trigger Inputs
- Wide Operating V_{CC} Range of 0.8 V to 3.6 V

- Optimized for 3.3-V Operation
- 3.6-V I/O Tolerant to Support Mixed-Mode Signal Operation
- $t_{pd} = 5.3 \text{ ns Max at } 3.3 \text{ V}$
- Suitable for Point-to-Point Applications
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 2000-V Human-Body Model (A114-B, Class II)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)
- ESD Protection Exceeds ±5000 V With Human-Body Model



See mechanical drawings for dimensions.

DESCRIPTION/ORDERING INFORMATION

The AUP family is TI's premier solution to the industry's low-power needs in battery-powered portable applications. This family ensures a very low static and dynamic power consumption across the entire V_{CC} range of 0.8 V to 3.6 V, resulting in an increased battery life. This product also maintains excellent signal integrity, which produces very low undershoot and overshoot characteristics.

ORDERING INFORMATION

T _A	PACKAGE ⁽¹⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING (2)	
	NanoStar™ – WCSP (DSBGA) 0.23-mm Large Bump – YEP	Tape and reel	SN74AUP1G57YEPR	Ш	
-40°C to 85°C	NanoFree [™] – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Tape and reel	SN74AUP1G57YZPR	HH_	
	SOT (SOT-23) - DBV	Tape and reel	SN74AUP1G57DBVR	HA7_	
	SOT (SC-70) - DCK	Tape and reel	SN74AUP1G57DCKR	HH_	
	SOT (SOT-553) - DRL	Reel of 4000	SN74AUP1G57DRLR	HH_	

- (1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.
- (2) DBV/DCK/DRL: The actual top-side marking has one additional character that designates the assembly/test site. YEP/YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, = Pb-free).



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

NanoStar, NanoFree are trademarks of Texas Instruments.

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DESCRIPTION/ORDERING INFORMATION (CONTINUED)

The SN74AUP1G57 features configurable multiple functions. The output state is determined by eight patterns of 3-bit input. The user can choose the logic functions AND, OR, NAND, NOR, XNOR, inverter, and noninverter. All inputs can be connected to V_{CC} or GND.

The device functions as an independent gate with Schmitt-trigger inputs, which allow for slow input transition and better switching noise immunity at the input.

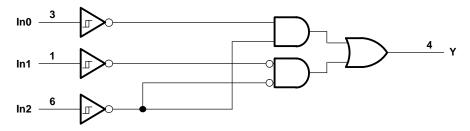
NanoStar[™] and NanoFree[™] package technology is a major breakthrough in IC packaging concepts, using the die as the package.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

FUNCTION TABLE

	INPUTS		OUTPUT
In2	ln1	In0	Y
L	L	L	Н
L	L	Н	L
L	Н	L	Н
L	Н	Н	L
Н	L	L	L
Н	L	Н	L
Н	Н	L	Н
Н	Н	Н	Н

LOGIC DIAGRAM (POSITIVE LOGIC)



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FUNCTION SELECTION TABLE

LOGIC FUNCTION	FIGURE NO.
2-input AND	1
2-input AND with both inputs inverted	4
2-input NAND with inverted input	2, 3
2-input OR with inverted input	2, 3
2-input NOR	4
2-input NOR with both inputs inverted	1
2-input XNOR	5

LOGIC CONFIGURATIONS

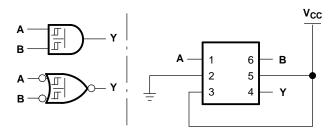
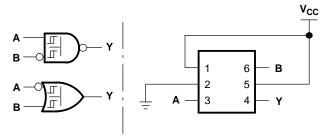


Figure 1. 2-Input AND Gate

Figure 2. 2-Input NAND Gate With Inverted A Input



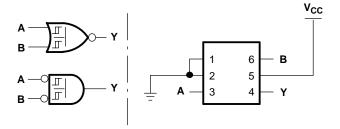


Figure 3. 2-Input NAND Gate With Inverted B Input

Figure 4. 2-Input NOR Gate

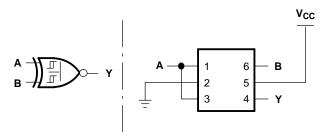


Figure 5. 2-Input XNOR Gate

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Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		-0.5	4.6	V
VI	Input voltage range (2)		-0.5	4.6	V
Vo	Voltage range applied to any output in the h	igh-impedance or power-off state (2)	-0.5	4.6	V
Vo	Output voltage range in the high or low state	9(2)	-0.5	V _{CC} + 0.5	V
I _{IK}	Input clamp current	V _I < 0		-50	mA
I _{OK}	Output clamp current	V _O < 0		-50	mA
Io	Continuous output current			±20	mA
	Continuous current through V _{CC} or GND			±50	mA
		DBV package		165	
0	Decke so the small impedance (3)	DCK package		259	°C/W
θ_{JA}	Package thermal impedance (3)	DRL package		142	C/VV
		YEP/YZP package		123	
T _{stg}	Storage temperature range		-65	150	°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

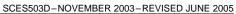
Recommended Operating Conditions⁽¹⁾

			MIN	MAX	UNIT	
V_{CC}	Supply voltage		0.8	3.6	V	
V_{I}	Input voltage		0	3.6	V	
Vo	Output voltage		0	V_{CC}	٧	
		V _{CC} = 0.8 V		-20	μΑ	
		V _{CC} = 1.1 V		-1.1		
	Input voltage Output voltage High-level output current Low-level output current	V _{CC} = 1.4 V		-1.7		
I _{OH}	nigh-level output current	V _{CC} = 1.65		0.8 3.6 V 0 3.6 V 0 V _{CC} V -20 μA -1.1		
		V _{CC} = 2.3 V				
		V _{CC} = 3 V		-4		
		V _{CC} = 0.8 V	0.8 3.6 0 3.6 0 V _{CC} -20 -1.1 -1.7 -1.9 -3.1 -4 20 1.1 1.7 1.9 3.1	20	μΑ	
		V _{CC} = 1.1 V		1.1		
	Low level output ourrent	V _{CC} = 1.4 V		1.7		
l _{OL}	Low-level output current	V _{CC} = 1.65 V		1.9	mA	
		V _{CC} = 2.3 V		3.1		
		V _{CC} = 3 V		4		
Δt/Δν	Input transition rise or fall rate	V _{CC} = 0.8 V to 3.6 V		200	ns/V	
T _A	Operating free-air temperature		-40	85	°C	

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed. The package thermal impedance is calculated in accordance with JESD 51-7.







over recommended operating free-air temperature range (unless otherwise noted)

DADAMETED	TEST SOMBITIONS		.,	T _A	= 25°C		T _A = -40°0	C to 85°C		
PARAMETER	TEST CONDITIONS		V _{cc}	MIN	TYP	MAX	MIN	MAX	UNIT	
			0.8 V	0.3		0.6	0.3	0.6		
V			1.1 V	0.53		0.9	0.53	0.9		
V _{T+} Positive-going			1.4 V	0.74		1.11	0.74	1.11	V	
input threshold			1.65 V	0.91		1.29	0.91	1.29	V	
voltage			2.3 V	1.37		1.77	1.37	1.77		
			3 V	1.88		2.29	1.88	2.29		
			0.8 V	0.1		0.6	0.1	0.6		
			1.1 V	0.26		0.65	0.26	0.65		
V _{T-} Negative-going			1.4 V	0.39		0.75	0.39	0.75	.,	
input threshold			1.65 V	0.47		0.84	0.47	0.84	V	
voltage			2.3 V	0.69		1.04	0.69	1.04		
			3 V	0.88		1.24	0.88	1.24		
			0.8 V	0.07		0.5	0.07	0.5		
ΔV_{T}			1.1 V	0.08		0.46	0.08	0.46		
			1.4 V	0.18		0.56	0.18	0.56		
Hysteresis			1.65 V	0.27		0.66	0.27	0.66	V	
$(V_T+ - V_T-)$			2.3 V	0.53		0.92	0.53	0.92		
			3 V	0.79		1.31	0.79	1.31		
	I _{OH} = -20 μA		0.8 V to 3.6 V	V _{CC} - 0.1			V _{CC} - 0.1			
	$I_{OH} = -1.1 \text{ mA}$		1.1 V	0.75 × V _{CC}			0.7 × V _{CC}			
	$I_{OH} = -1.7 \text{ mA}$		1.4 V	1.11			1.03			
	$I_{OH} = -1.9 \text{ mA}$		1.65 V	1.32			1.3			
V_{OH}	$I_{OH} = -2.3 \text{ mA}$			2.05			1.97		V	
	$I_{OH} = -3.1 \text{ mA}$		2.3 V	1.9			1.85			
	$I_{OH} = -2.7 \text{ mA}$			2.72			2.67			
	$I_{OH} = -4 \text{ mA}$		3 V	2.6			2.55			
	$I_{OL} = 20 \mu\text{A}$		0.8 V to 3.6 V	2.0		0.1	2.00	0.1		
						0.3 ×				
	I _{OL} = 1.1 mA		1.1 V			V_{CC}		0.3 × V _{CC}		
	I _{OL} = 1.7 mA		1.4 V			0.31		0.37		
V _{OL}	$I_{OL} = 1.9 \text{ mA}$		1.65 V			0.31		0.35	V	
	$I_{OL} = 2.3 \text{ mA}$		2.3 V			0.31		0.33		
	$I_{OL} = 3.1 \text{ mA}$		2.5 V			0.44		0.45		
	$I_{OL} = 2.7 \text{ mA}$		3 V			0.31		0.33		
	I _{OL} = 4 mA		3 V			0.44		0.45		
I _I All inputs	$V_I = GND \text{ to } 3.6 \text{ V}$		0 V to 3.6 V	-		0.1	·	0.5	μΑ	
l _{off}	V_I or $V_O = 0$ V to 3.6 V		0 V			0.2		0.6	μΑ	
$\Delta I_{ m off}$	V_I or $V_O = 0$ V to 3.6 V		0 V to 0.2 V			0.2		0.6	μΑ	
I _{CC}	$V_I = GND \text{ or } (V_{CC} \text{ to } 3.6 \text{ V}),$	I _O = 0	0.8 V to 3.6 V			0.5		0.9	μΑ	
ΔI_{CC}	$V_I = V_{CC} - 0.6 V^{(1)},$	I _O = 0	3.3 V			40		50	μΑ	
		-	0 V		1.5				•	
C _i	$V_I = V_{CC}$ or GND		3.6 V		1.5				pF	
C _o	V _O = GND		0 V		3				pF	

⁽¹⁾ One input at V_{CC} – 0.6 V, other inputs at V_{CC} or GND

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Switching Characteristics

over recommended operating free-air temperature range, $C_L = 5 \text{ pF}$ (unless otherwise noted) (see Figure 6 and Figure 7)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V	$T_A = 25^{\circ}C$			$T_A = -40$ °C to 85°C		UNIT
TANAMETER			V _{cc}	MIN	TYP	MAX	MIN	MAX	ONII
			0.8 V		28.6				
		V	1.2 V ± 0.1 V	2.6	9.5	13.6	2.1	17.1	
	In0, In1, or In2		1.5 V ± 0.1 V	1.9	6.4	9.1	1.4	11.1	no
t _{pd}	1110, 1111, 01 1112	ı	1.8 V ± 0.15 V	1.4	5.2	7.1	0.9	8.9	ns
			2.5 V ± 0.2 V	1.1	3.6	5.3	0.6	6.3	
			3.3 V ± 0.3 V	1	2.9	4.4	0.5	5.3	

Switching Characteristics

over recommended operating free-air temperature range, $C_L = 10 \text{ pF}$ (unless otherwise noted) (see Figure 6 and Figure 7)

PARAMETER	FROM	TO (OUTPUT)	V	T _A = 25°C			T _A = -40°C to 85°C		UNIT
PARAMETER	(INPUT)		V _{cc}	MIN	TYP	MAX	MIN	MAX	UNIT
			0.8 V		32.8				
	In0, In1, or In2	Y	1.2 V ± 0.1 V	2.6	11	15.1	2.1	18.1	ns
			1.5 V ± 0.1 V	1.9	7.4	10.3	1.4	12.4	
t _{pd}			1.8 V ± 0.15 V	1.4	6	8.1	0.9	10	
			2.5 V ± 0.2 V	1.1	4.3	6.1	0.6	7.3	
			3.3 V ± 0.3 V	1	3.5	5.1	0.5	6.1	

Switching Characteristics

over recommended operating free-air temperature range, $C_L = 15 \text{ pF}$ (unless otherwise noted) (see Figure 6 and Figure 7)

PARAMETER	FROM	то	V	T _A	= 25°C		$T_A = -40^{\circ}C t$	o 85°C	UNIT
FARAMETER	(INPUT)	(OUTPUT)	V _{cc}	MIN	TYP	MAX	MIN	MAX	UNII
			0.8 V		37				
	ln0, ln1, or ln2	Y	1.2 V ± 0.1 V	3.6	12.3	16.8	3.1	20.1	
_			1.5 V ± 0.1 V	2.8	8.3	11.4	2.3	13.7	
t _{pd}			1.8 V ± 0.15 V	2.1	6.7	9	1.6	11.1	ns
			2.5 V ± 0.2 V	1.7	4.9	6.8	1.2	8.1	
			3.3 V ± 0.3 V	1.5	3.9	5.6	1	6.7	

Switching Characteristics

over recommended operating free-air temperature range, C_L = 30 pF (unless otherwise noted) (see Figure 6 and Figure 7)

PARAMETER	FROM	FROM TO (OUTPUT)	V	$T_A = 25^{\circ}C$			T _A = -40°C	to 85°C	LINUT
PARAMETER	(INPUT)		V _{cc}	MIN	TYP	MAX	MIN	MAX	UNIT
			0.8 V		49.3				
	In0, In1, or In2	Y	1.2 V ± 0.1 V	5	15.7	21.4	4.5	26.5	
			1.5 V ± 0.1 V	3.9	10.8	14.4	3.4	17.4	
t _{pd}			1.8 V ± 0.15 V	3.1	8.8	11.4	2.6	14	ns
			2.5 V ± 0.2 V	2.6	6.4	8.4	2.1	10.1	
			3.3 V ± 0.3 V	2.3	5.3	7	1.8	8.4	



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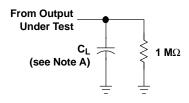
Operating Characteristics

 $T_A = 25^{\circ}C$

	PARAMETER	TEST CONDITIONS	V _{cc}	TYP	UNIT
			0.8 V	4	
			1.2 V ± 0.1 V	4	
_	Dower discinction conscitones	f = 10 MHz	1.5 V ± 0.1 V	4	
C _{pd}	Power dissipation capacitance		1.8 V ± 0.15 V	4	pF
			2.5 V ± 0.2 V	4.1	
			3.3 V ± 0.3 V	4.3	

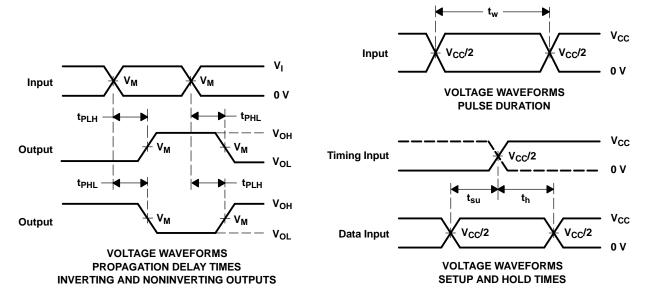


PARAMETER MEASUREMENT INFORMATION (Propagation Delays, Setup and Hold Times, and Pulse Duration)



LOAD CIRCUIT

	V _{CC} = 0.8 V	V _{CC} = 1.2 V ± 0.1 V	V _{CC} = 1.5 V ± 0.1 V	V _{CC} = 1.8 V ± 0.15 V	V_{CC} = 2.5 V \pm 0.2 V	V _{CC} = 3.3 V ± 0.3 V
C _L	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF	5, 10, 15, 30 pF
V _M	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{CC} /2	V _{CC} /2
V _I	V _{CC}	V _{CC}	V _{CC}	V _{CC}	V _{CC}	V _{CC}



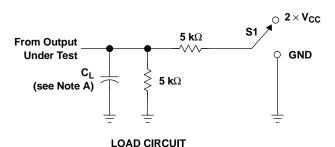
NOTES: A. C_L includes probe and jig capacitance.

- B. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{O} = 50 Ω , slew rate \geq 1 V/ns.
- C. The outputs are measured one at a time, with one transition per measurement.
- D. t_{PLH} and t_{PHL} are the same as t_{pd} .
- E. All parameters and waveforms are not applicable to all devices.

Figure 6. Load Circuit and Voltage Waveforms

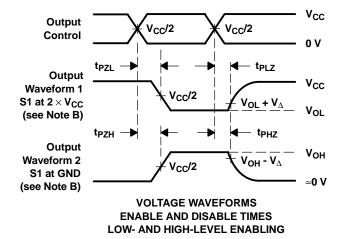
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PARAMETER MEASUREMENT INFORMATION (Enable and Disable Times)



TEST	S1
t _{PLZ} /t _{PZL}	2×V _{CC}
t _{PHZ} /t _{PZH}	GND

 $V_{CC} = 1.2 \text{ V}$ $V_{CC} = 1.5 V$ $V_{CC} = 1.8 \text{ V}$ $V_{CC} = 2.5 \text{ V}$ $V_{CC} = 3.3 V$ $V_{CC} = 0.8 V$ \pm 0.1 V \pm 0.1 V \pm 0.15 V \pm 0.2 V $\pm\,$ 0.3 V 5, 10, 15, 30 pF 5, 10, 15, 30 pF 5, 10, 15, 30 pF C_L 5, 10, 15, 30 pF 5, 10, 15, 30 pF 5, 10, 15, 30 pF V_{M} V_{CC}/2 V_{CC}/2 V_{CC}/2 V_{CC}/2 V_{CC}/2 V_{CC}/2 V_{I} V_{CC} v_{cc} V_{CC} V_{CC} V_{CC} V_{CC} 0.1 V 0.15 V 0.15 V 0.3 V V_{Δ} 0.1 V 0.1 V



- NOTES: A. C_I includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{O} = 50 Ω , slew rate \geq 1 V/ns.
 - D. The outputs are measured one at a time, with one transition per measurement.
 - E. t_{PL7} and t_{PH7} are the same as t_{dis}.
 - F. t_{PZL} and t_{PZH} are the same as t_{en} .
 - G. All parameters and waveforms are not applicable to all devices.

Figure 7. Load Circuit and Voltage Waveforms







PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
SN74AUP1G57DBVR	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G57DBVRE4	ACTIVE	SOT-23	DBV	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G57DBVT	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G57DBVTE4	ACTIVE	SOT-23	DBV	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G57DCKR	ACTIVE	SC70	DCK	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G57DCKRE4	ACTIVE	SC70	DCK	6	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G57DCKT	ACTIVE	SC70	DCK	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G57DCKTE4	ACTIVE	SC70	DCK	6	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G57DRLR	ACTIVE	SOP	DRL	6	4000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN74AUP1G57YEPR	ACTIVE	WCSP	YEP	6	3000	TBD	SNPB	Level-1-260C-UNLIM
SN74AUP1G57YZPR	ACTIVE	WCSP	YZP	6	3000	Pb-Free (RoHS)	SNAGCU	Level-1-260C-UNLIM

 $^{(1)}$ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS) or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

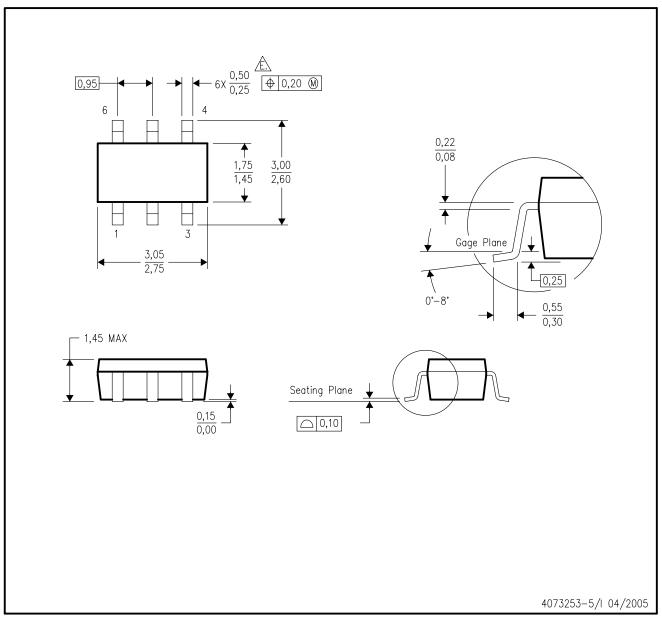
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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DBV (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE



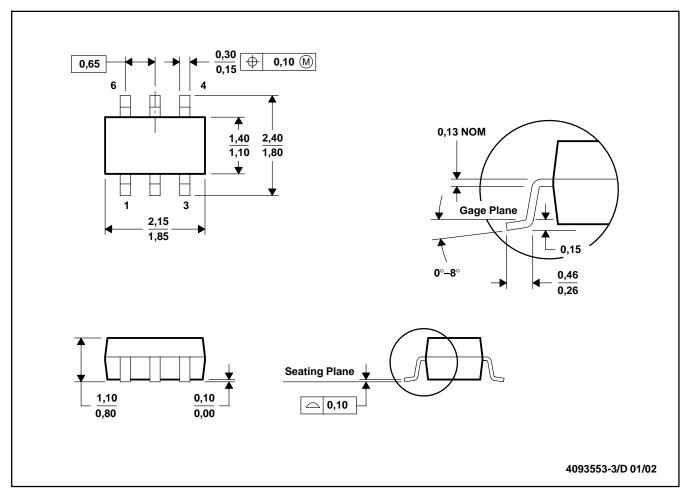
NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- Falls within JEDEC MO-178 Variation AB, except minimum lead width.



DCK (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE

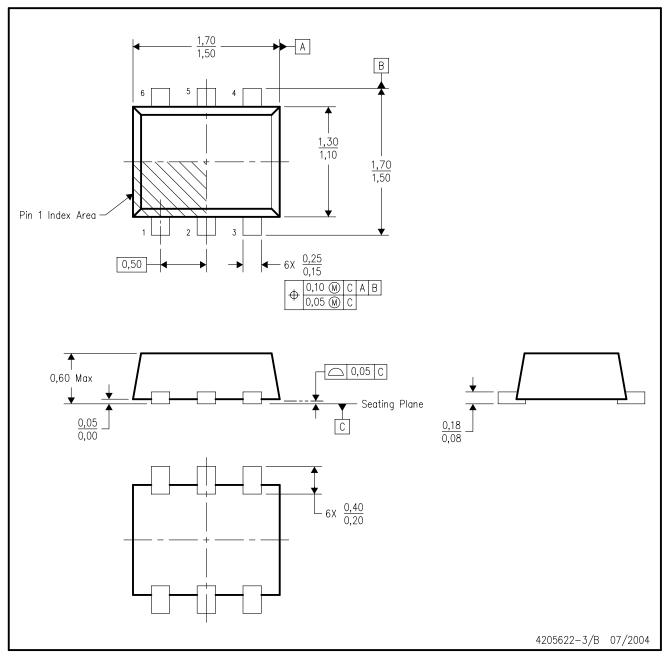


NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO-203

DRL (R-PDSO-N6)

PLASTIC SMALL OUTLINE



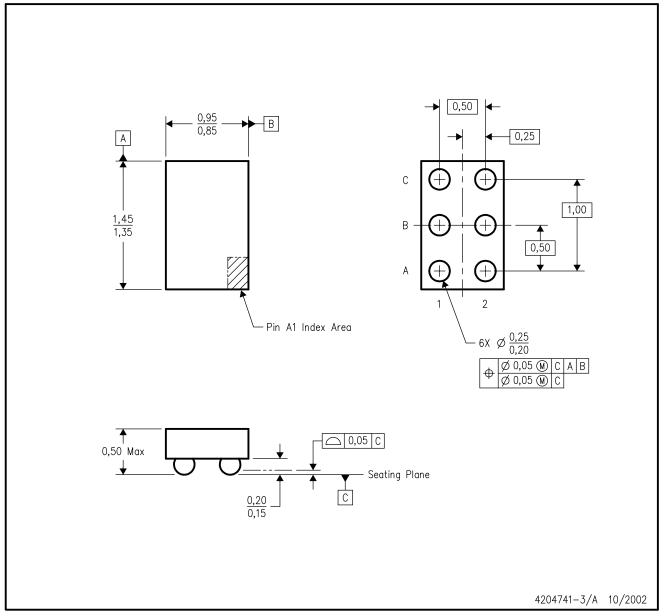
NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. JEDEC package registration is pending.



YZP (R-XBGA-N6)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

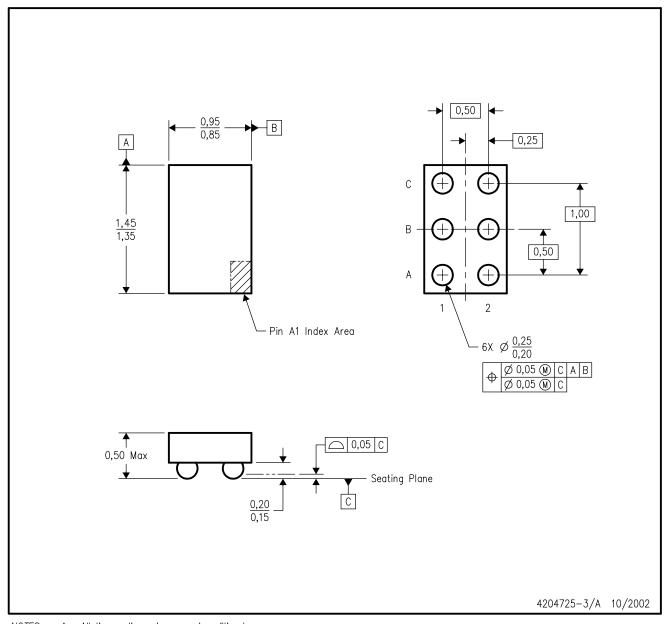
- B. This drawing is subject to change without notice.
- C. NanoFree™ package configuration.
- D. This package is lead-free. Refer to the 6 YEP package (drawing 4204725) for tin-lead (SnPb).

NanoFree is a trademark of Texas Instruments.



YEP (R-XBGA-N6)

DIE-SIZE BALL GRID ARRAY



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. NanoStar \mathbf{M} package configuration.
- D. This package is tin-lead (SnPb). Refer to the 6 YZP package (drawing 4204741) for lead-free.

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